

MOSFET, Power; N-Ch; VDSS 40V; RDS(ON) 1.8Milliohms; ID 280A; TO-220AB; PD 330W; -55de

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220AB
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF2804PBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

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This HEXFET®Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

Features

Optimized for broadest availability from distribution partners

Product qualification according to JEDEC standard

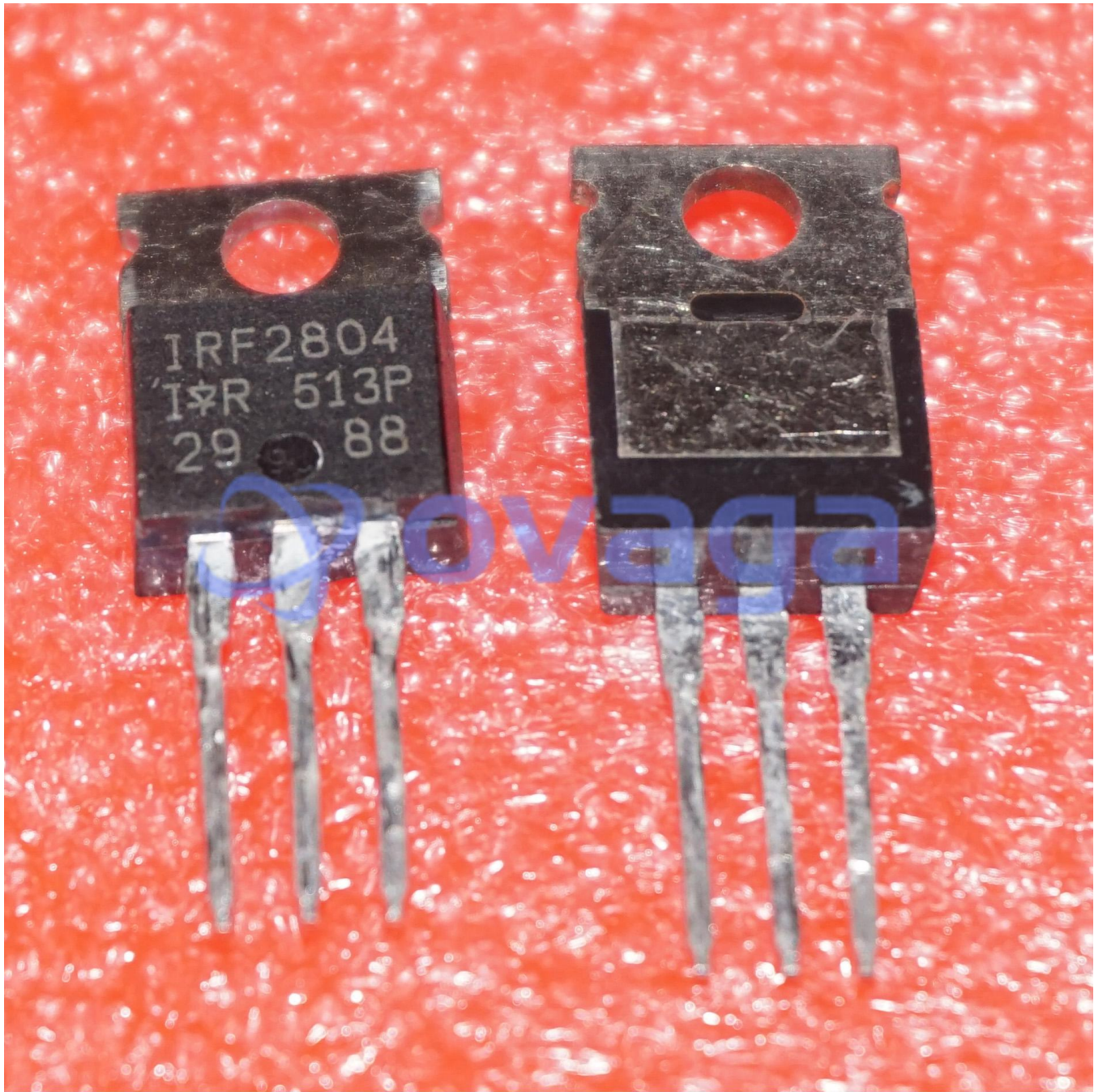
Normal level : Optimized for 10 V gate drive voltage

Industry standard surface-mount power package

Higher current-rating (by 23%) vs D2PAK (of same die-size)

High-current carrying capability package (up to 240 A, die-size dependent)



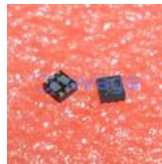


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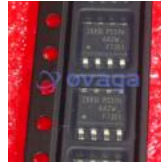
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